

**Product Summary**

Device	V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
Q1	30V	25mΩ @ V <sub>GS</sub> = 10V	6.5A
		29mΩ @ V <sub>GS</sub> = 4.5V	6.1A
Q2	-30V	28mΩ @ V <sub>GS</sub> = -10V	-6.2A
		38mΩ @ V <sub>GS</sub> = -4.5V	-5.3A

**Description**

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

- DC-DC Converters
- Power Management Functions
- Backlighting

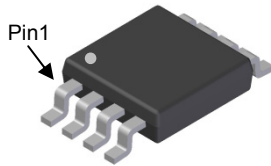
**Features and Benefits**

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

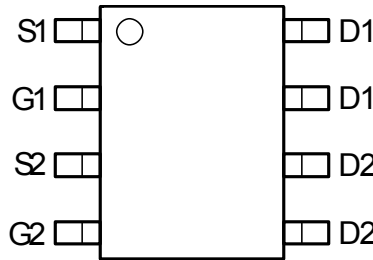
**Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.074 grams (approximate)

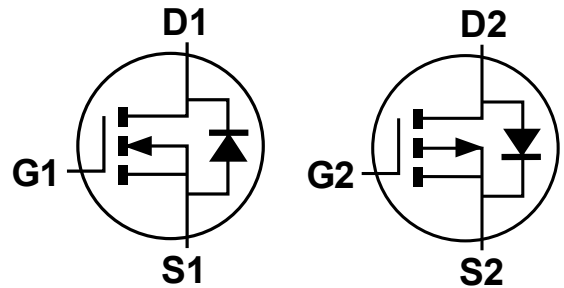
NEW PRODUCT



Top View



Top View  
Pin Configuration



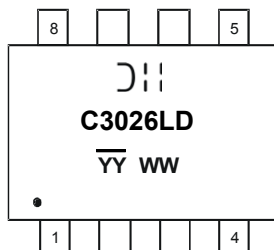
Equivalent Circuit

**Ordering Information** (Note 4)

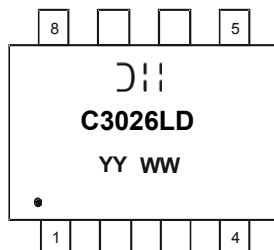
Part Number	Case	Packaging
DMC3026LSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



Chengdu A/T Site



Shanghai A/T Site

- ☺ = Manufacturer's Marking
- C3026LD = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Year (ex: 14 = 2014)
- WW = Week (01 - 53)
- YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
- YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

**Maximum Ratings – Q1 and Q2** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Q1	Q2	Units		
Drain-Source Voltage	V <sub>DSS</sub>	30	-30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	±20	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.5 5.2	-6.2 -5.0	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	8.2 6.7	-8.0 -6.5	A
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	2.2	-2.5	A		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	40	-40	A		
Avalanche Current (Notes 7) L = 0.1mH	I <sub>AS</sub>	14.5	22	A		
Avalanche Energy (Notes 7) L = 0.1mH	E <sub>AS</sub>	10.5	25	mJ		

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.2
		T <sub>A</sub> = +70°C	0.8
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	Steady state	102
		t < 10s	62
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.6
		T <sub>A</sub> = +70°C	1.0
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady state	78
		t < 10s	47
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	14.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics – Q1** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	19	25	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A
		—	22	29		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.3A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	641	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	66	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	51	—		
Gate Resistance	R <sub>G</sub>	—	2.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	6	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	13.2	—		
Gate-Source Charge	Q <sub>gs</sub>	—	1.7	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.2	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	3.3	—	nS	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 15V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>r</sub>	—	4.4	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	22.3	—		
Turn-Off Fall Time	t <sub>f</sub>	—	5.3	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - UIS in production with L = 0.1mH, starting T<sub>A</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

**Electrical Characteristics – Q2** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	—	-3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	21	28	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -6A
		—	29	38		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.3A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	1241	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	146	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	110	—		
Gate Resistance	R <sub>G</sub>	—	14.8	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	10.9	—	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -7A
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	22	—		
Gate-Source Charge	Q <sub>gs</sub>	—	3.5	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	4.7	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	9.7	—	nS	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -15V, R <sub>GEN</sub> = 6Ω, I <sub>D</sub> = -7A
Turn-On Rise Time	t <sub>r</sub>	—	17.1	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	60.5	—		
Turn-Off Fall Time	t <sub>f</sub>	—	40.4	—		

- Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

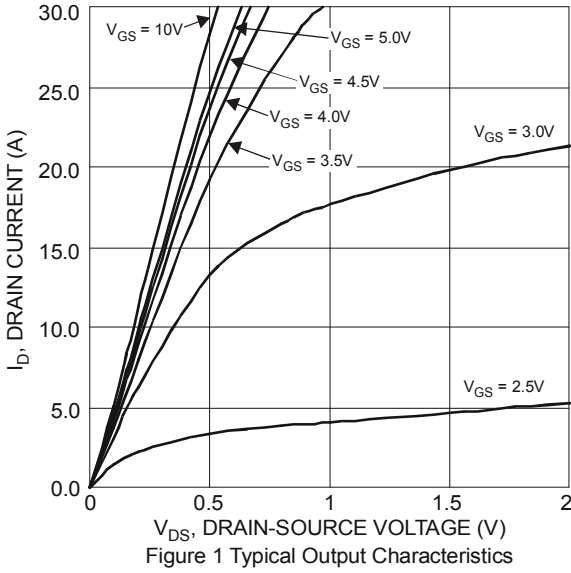


Figure 1 Typical Output Characteristics

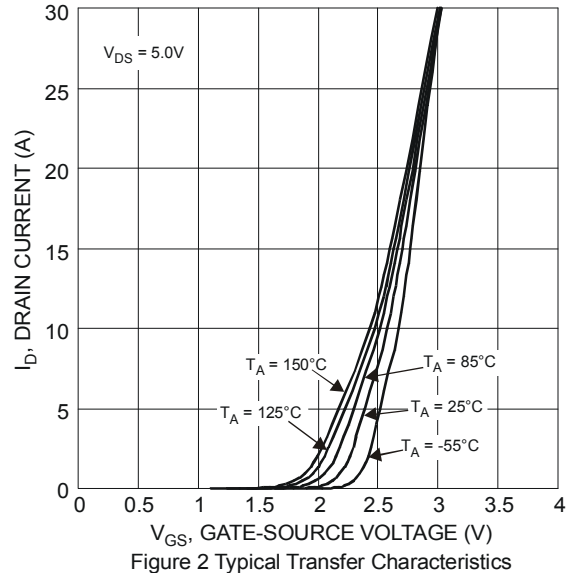


Figure 2 Typical Transfer Characteristics

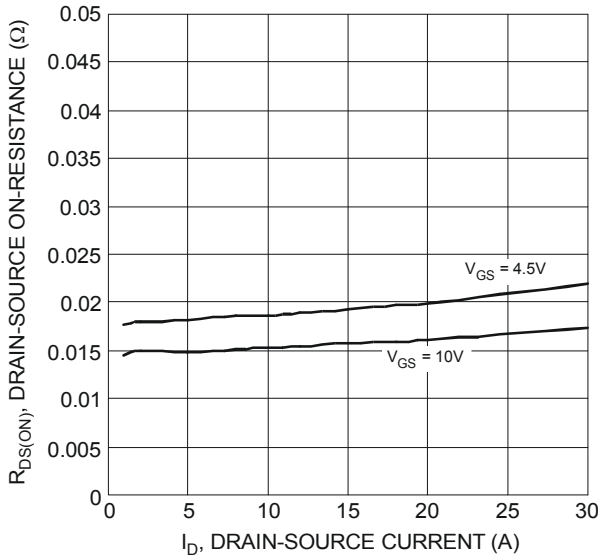


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

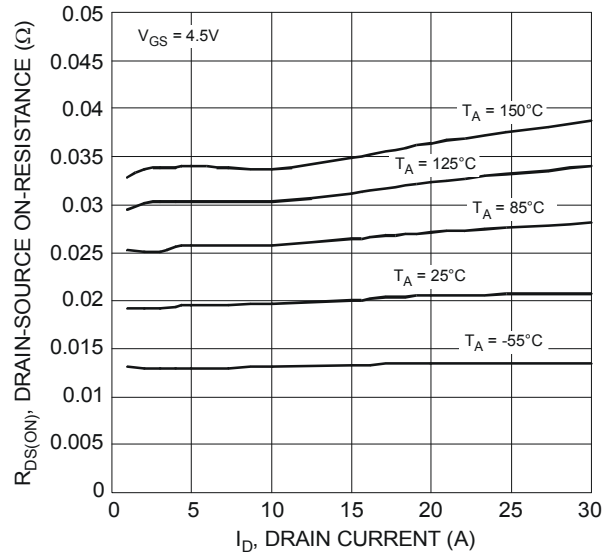


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

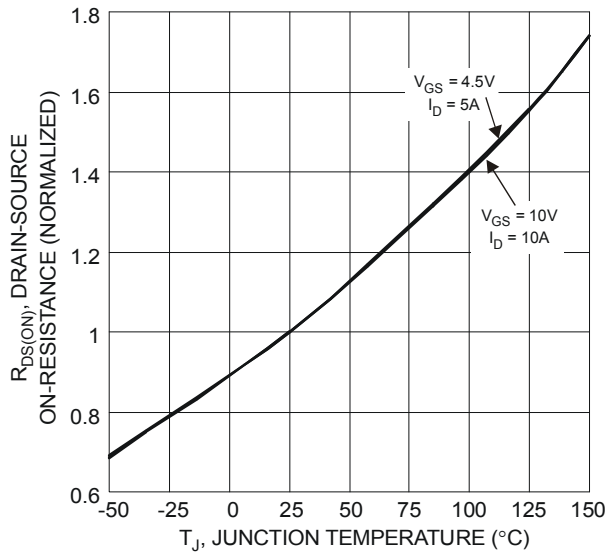


Figure 5 On-Resistance Variation with Temperature

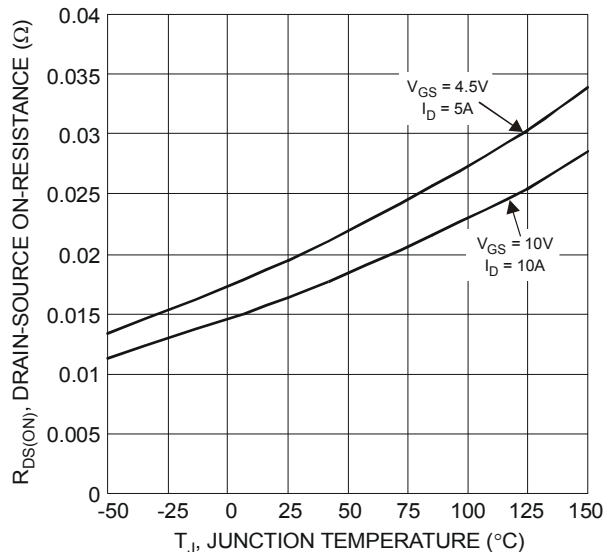


Figure 6 On-Resistance Variation with Temperature

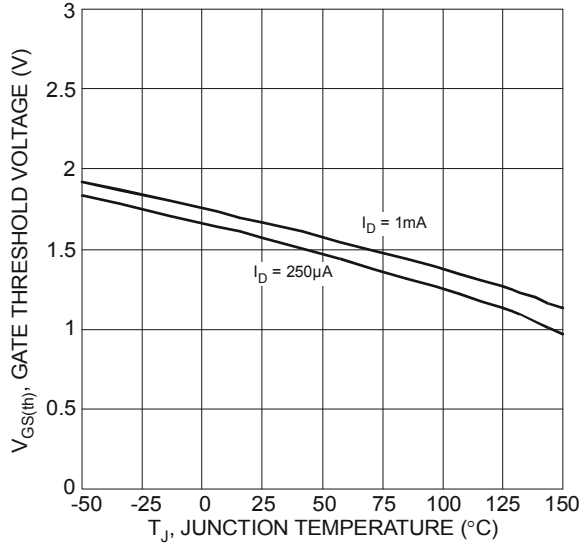


Figure 7 Gate Threshold Variation vs. Ambient Temperature

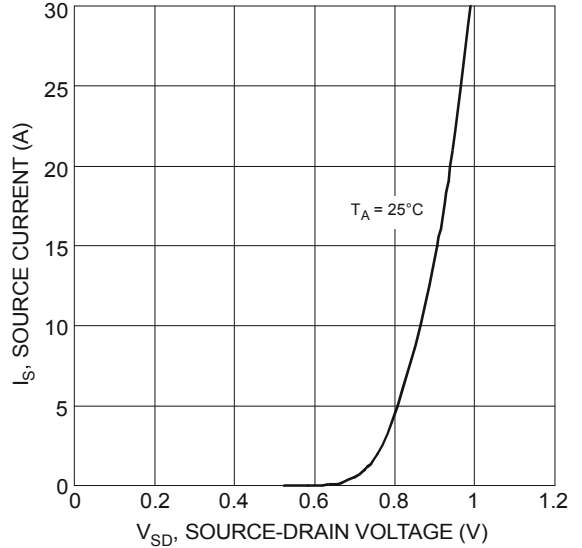


Figure 8 Diode Forward Voltage vs. Current

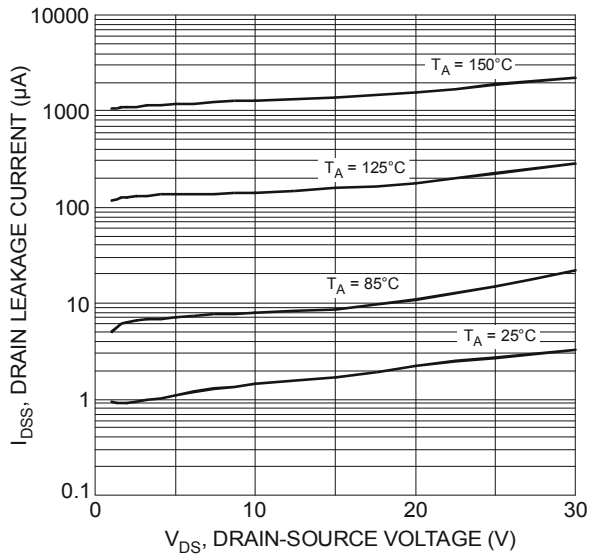


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

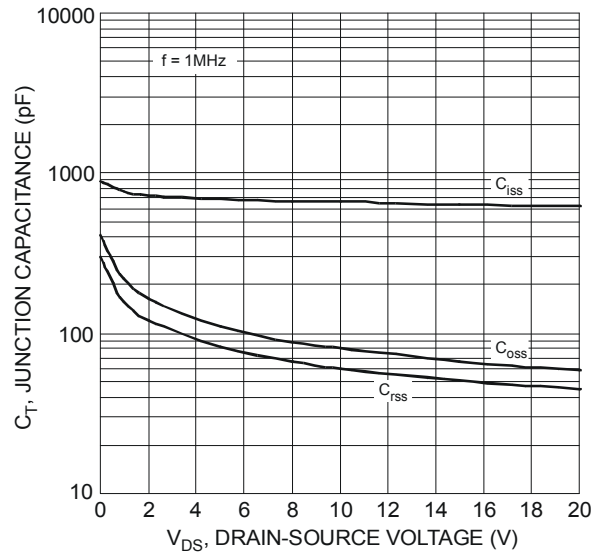


Figure 10 Typical Junction Capacitance

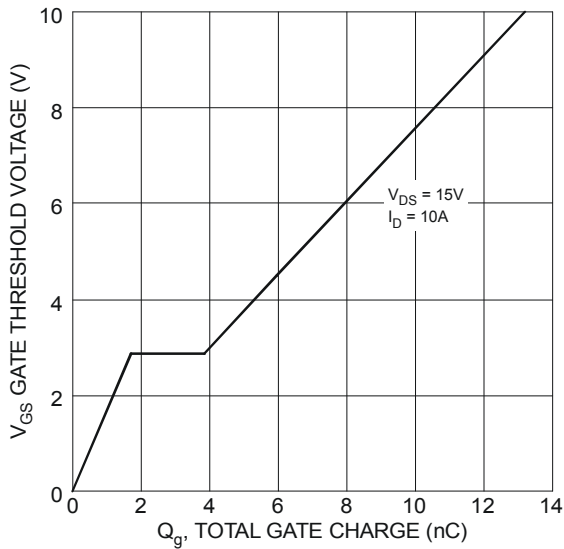


Figure 11 Gate Charge

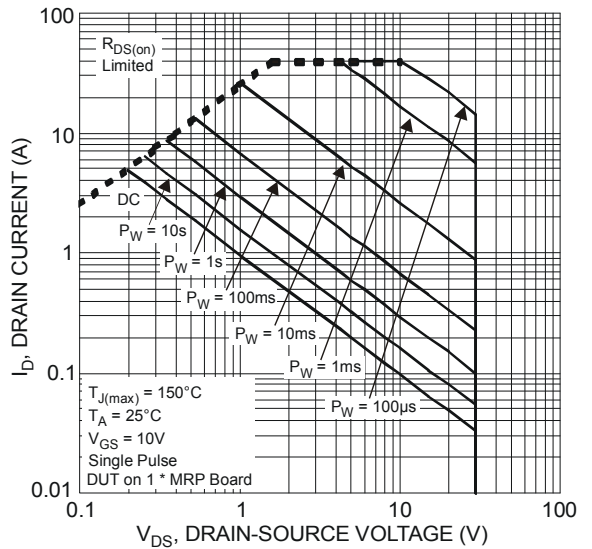


Figure 12 SOA, Safe Operation Area

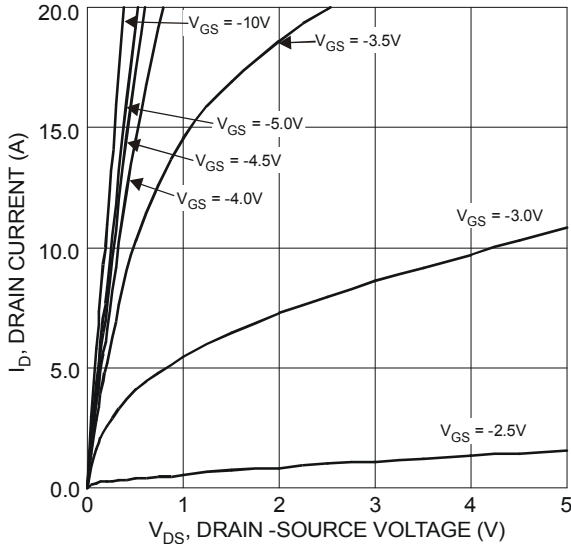


Figure 13 Typical Output Characteristics

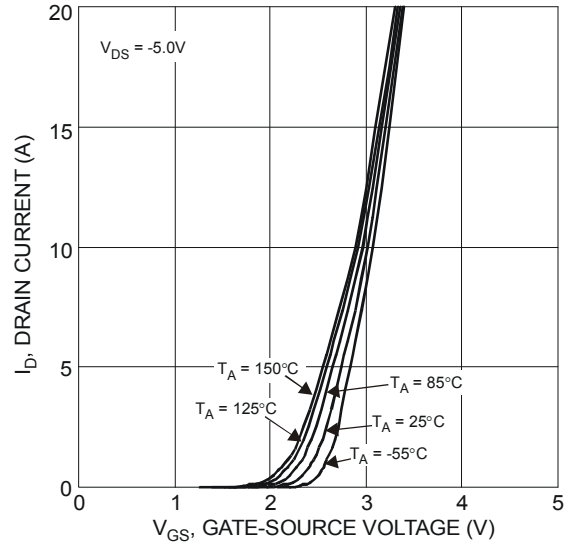


Figure 14 Typical Transfer Characteristics

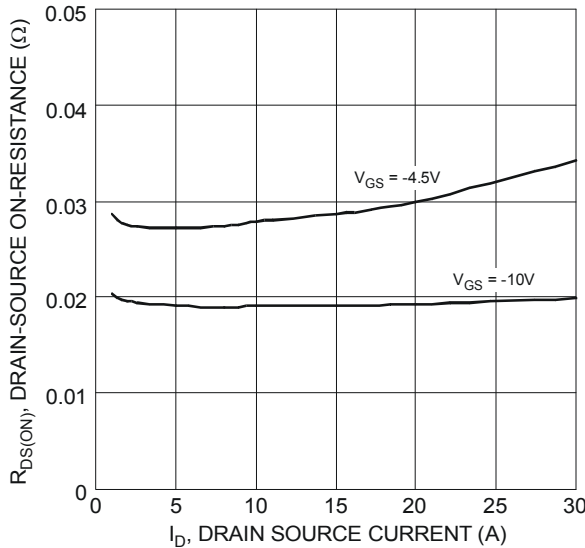


Figure 15 Typical On-Resistance vs. Drain Current and Gate Voltage

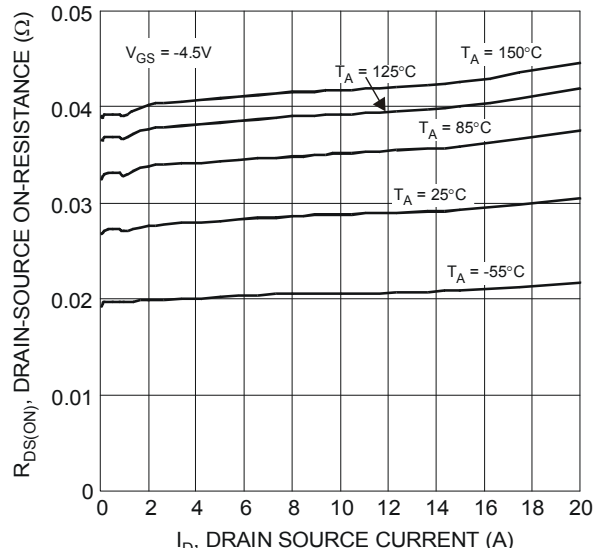


Figure 16 Typical On-Resistance vs. Drain Current and Temperature

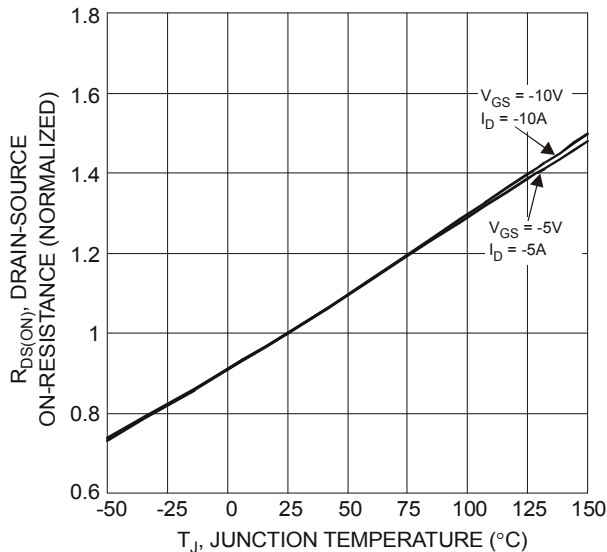


Figure 17 On-Resistance Variation with Temperature

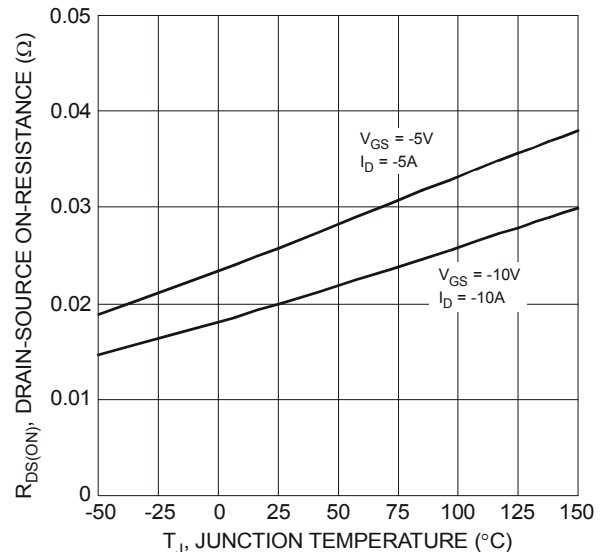


Figure 18 On-Resistance Variation with Temperature

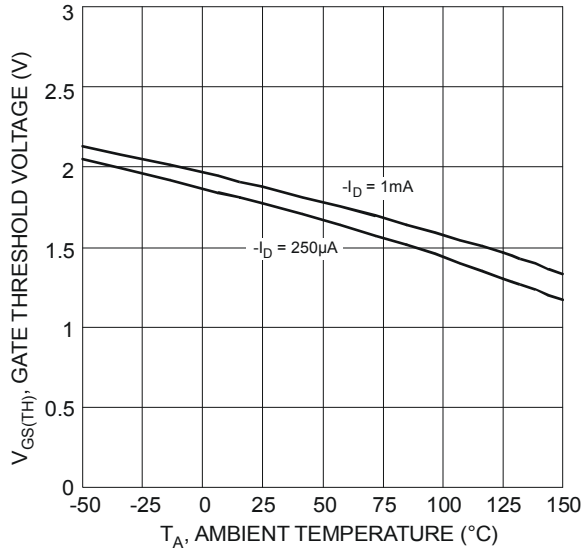


Figure 19 Gate Threshold Variation vs. Ambient Temperature

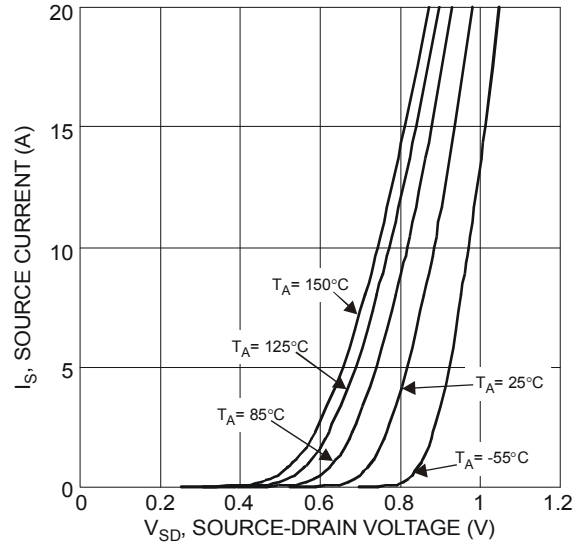


Figure 20 Diode Forward Voltage vs. Current

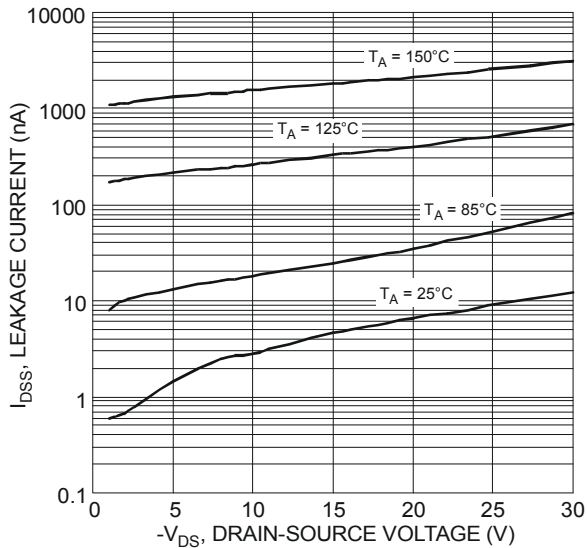


Figure 21 Typical Drain-Source Leakage Current vs. Voltage

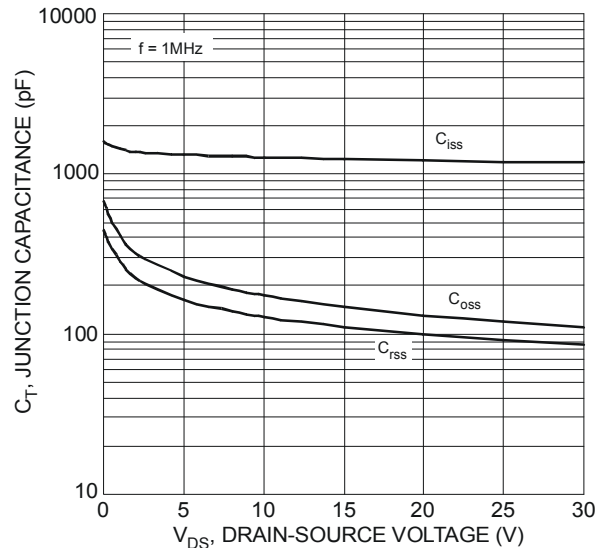


Figure 22 Typical Junction Capacitance

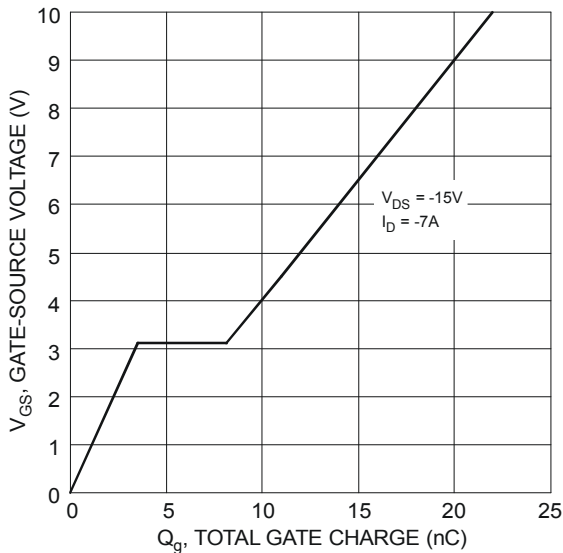


Figure 23 Gate-Charge Characteristics

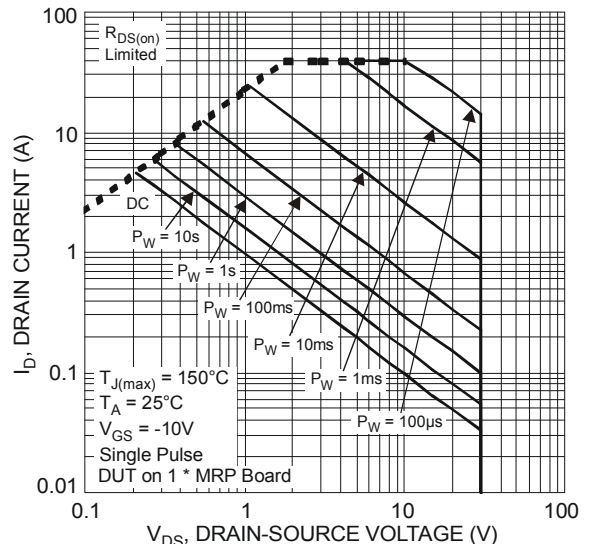
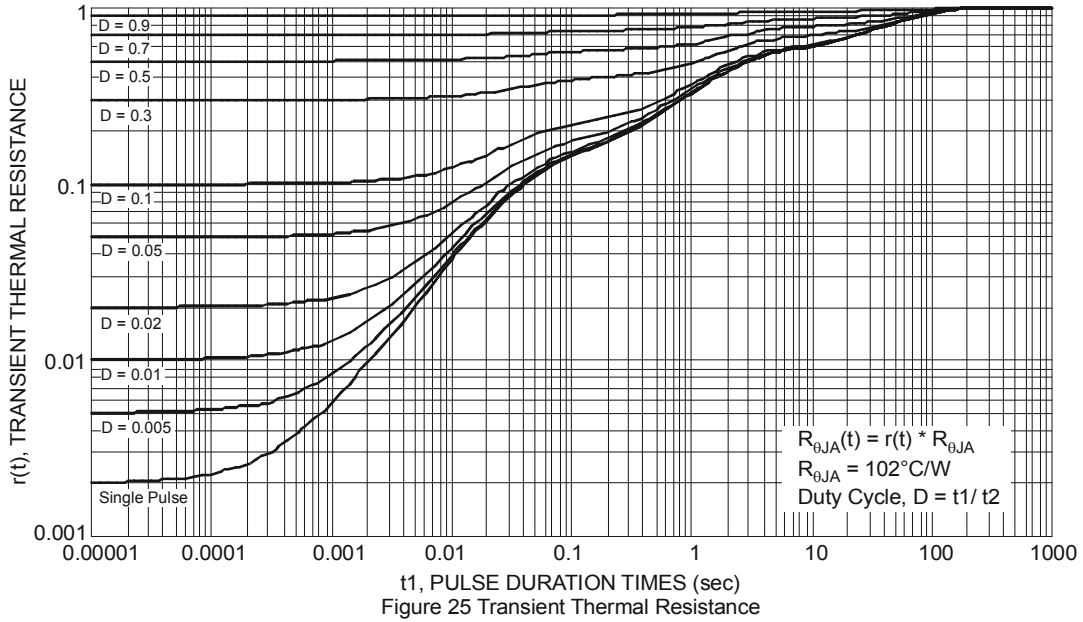
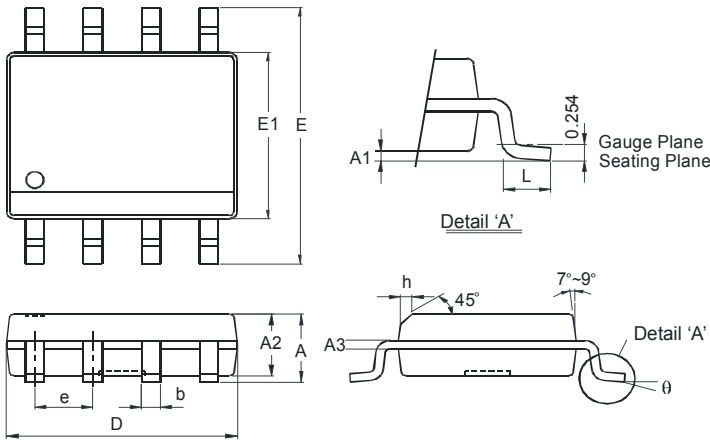


Figure 24 SOA, Safe Operation Area



**Package Outline Dimensions**

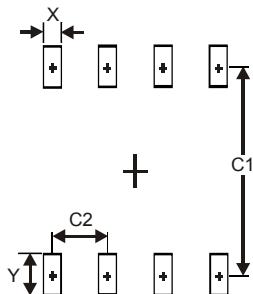
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27



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